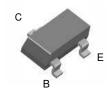


May 2009

FSB560/FSB560A NPN Low Saturation Transistor

Features

 These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.



SuperSOT[™]-3 (SOT-23)

Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{CBO}	Collector-Base Voltage 80		V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current - Continuous 2		Α	
T_J, T_{STG}	Operating and Storage Junction Temperature Range - 55 to +150		°C	

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Ма	Lleito	
		FSB560	FSB560A	Units
P_{D}	Total Device Dissipation	500		mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250		°C/W

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter Test Conditions		Min.	Max.	Units
Off Characteristics					
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A$	80		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\mu A$	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30V V _{CB} = 30V, T _A = 100°C		100 10	nA μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
On Characteristics*					
h _{FE}	DC Current Gain	$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	70 100 250 80 40	300 550	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I_{C} = 1A, I_{B} = 100mA I_{C} = 2A, I_{B} = 200mA FSB560 FSB560A		300 350 300	mV mV mV
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 1A, I _B = 100mA		1.25	V
V _{BE} (on)	Base-Emitter On Voltage	I _C = 1A, V _{CE} = 2V		1	V
Small Sig	nal Characteristics				
C _{obo}	Output Capacitance	V _{CB} = 10V, I _E = 0, f = 1MHz		30	pF
f _T	Transition Frequency	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	75		MHz

^{*} Pulse Test: Pulse Width $\leq 300 \mu s, \ Duty \ Cycle \leq 2.0\%$

Typical Performance Characteristics

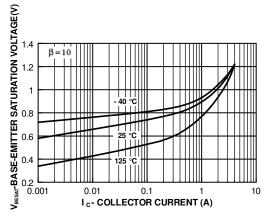


Figure 1. Base-Emitter Saturation Voltage vs Collector Current

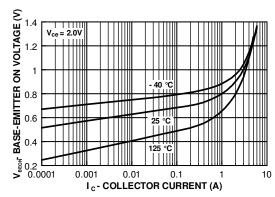


Figure 2. Base-Emitter On Voltage vs Collector Current

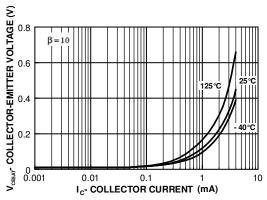


Figure 3. Collector-Emitter Saturation Voltage vs Collector Current

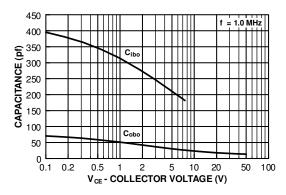


Figure 4. Input/Output Capacitance vs Reverse Bias Voltage

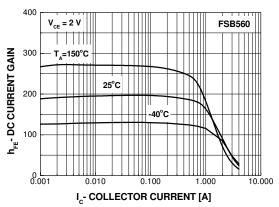


Figure 5. Current Gain vs Collector Current

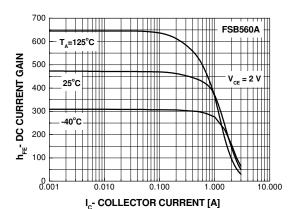
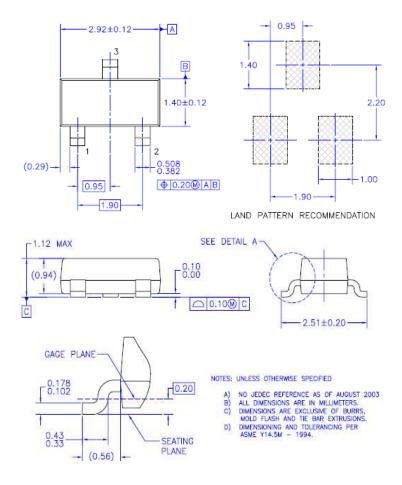


Figure 6. Current Gain vs Collector Current

Physical Dimensions

SuperSOT-23







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Definition of Terms			
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